L	Hits	Search Text	DB	Time stamp
Number				
_	29676	magnetic near2 memory	USPAT; US-PGPUB;	2004/06/27 23:21
			EPO; JPO; DERWENT; IBM TDB	
-	13267	conductive adj line	USPAT; US-PGPUB; EPO; JPO;	2004/06/27 22:57
_	121130		DERWENT; IBM_TDB USPAT;	2004/06/27
,		adj2 line) or ((bit or word) adj line)	US-PGPUB; EPO; JPO; DERWENT;	22:59
_	2237	(magnetic near2 memory) and ((conductive adj2 line) or (electrical adj2 line) or ((bit or word) adj line))	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/06/27 22:59
-	41703	magnetic near3 memory	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/06/27 23:43
-	2840	(magnetic near3 memory) and ((conductive adj2 line) or (electrical adj2 line) or ((bit or word) adj line))	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/06/27 23:44
_	183281	(current adj2 supply) or (voltage adj2 supply)	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/06/27 23:55
-	368	adj2 line) or (electrical adj2 line) or ((bit or word) adj line))) and ((current	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/06/27 23:46
_	164738	adj2 supply) or (voltage adj2 supply))  current with direction	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/06/28 00:31
	46893	multipl\$4 near2 line	DERWENT; IBM_TDB USPAT;	2004/06/28
			US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	00:32
-	34	<pre>((magnetic near3 memory) and (((magnetic near3 memory) and ((conductive adj2 line) or (electrical adj2 line) or ((bit or word) adj line))) and ((current adj2 supply) or (voltage adj2 supply)))) and (multipl\$4 near2 line)</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/28
_	368	<pre>(magnetic near3 memory) and (((magnetic near3 memory) and ((conductive adj2 line) or (electrical adj2 line) or ((bit or word) adj line))) and ((current adj2</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/06/28 01:06
-	688	supply) or (voltage adj2 supply))) magnetic adj memory adj cell\$1	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/06/28 01:07
			DERWENT; IBM TDB	

-	534	(magnetic adj memory adj cell\$1) and line	USPAT;	2004/06/28
			US-PGPUB;	01:07
			EPO; JPO;	
			DERWENT;	<u> </u>
			IBM TDB	
-	109	((magnetic adj memory adj cell\$1) and	USPAT;	2004/06/28
		line) and current adj source	US-PGPUB;	01:08
			EPO; JPO;	1
			DERWENT;	
			IBM TDB	
_	2167	mram and line	USPAT;	2004/06/28
-	2107	mram and rine	US-PGPUB;	01:08
			EPO; JPO;	01.00
				l i
			DERWENT;	
			IBM_TDB	0004/05/00
-	1163	(mram and line) and source	USPAT;	2004/06/28
			US-PGPUB;	01:08
			EPO; JPO;	]
			DERWENT;	İ
			IBM_TDB	1
-	633	((mram and line) and source) and supply	USPAT;	2004/06/28
			US-PGPUB;	01:09
			EPO; JPO;	1
			DERWENT;	1
			IBM TDB	1
_	753	((mram and line) and source) and suppl\$4	USPAT;	2004/06/28
		, ((,	US-PGPUB;	01:09
			EPO; JPO;	01.05
			DERWENT;	
	i		IBM TDB	
1_	508	(((mram and line) and source) and	USPAT;	2004/06/28
	300	suppl\$4) and 365/\$.ccls.	•	01:10
•		supprogramme sostoreers.	US-PGPUB;	01:10
[			EPO; JPO;	
			DERWENT;	1
	252		IBM_TDB	0004/00/55
~	252	((((mram and line) and source) and	USPAT;	2004/06/28
		suppl\$4) and 365/\$.ccls.) and (chang\$3	US-PGPUB;	01:27
		with direct\$4)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	1
-	168	((((mram and line) and source) and	USPĀT;	2004/06/28
		suppl\$4) and 365/\$.ccls.) and (chang\$3	US-PGPUB;	01:27
		with direct\$4 with current)	EPO; JPO;	
!			DERWENT;	
			IBM TDB	1